

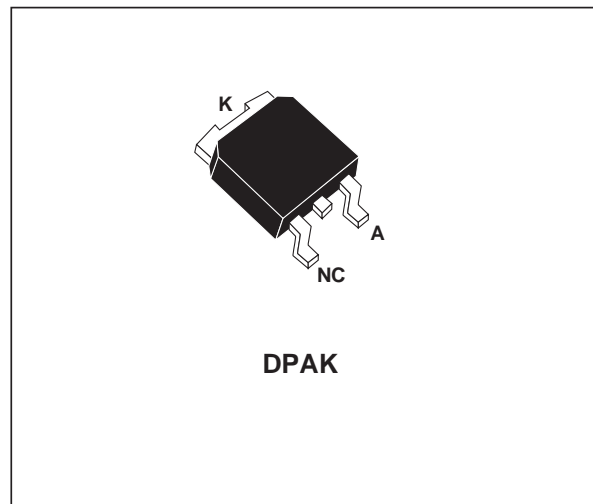
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	5 A
V_{RRM}	100 V
$T_j(\text{max})$	175 °C
$V_F(\text{max})$	0.61 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- HIGH JUNCTION TEMPERATURE CAPABILITY
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- AVALANCHE CAPABILITY SPECIFIED



DESCRIPTION

Schottky barrier rectifier designed for high frequency miniature Switched Mode Power Supplies such as adaptators and on board DC to DC converters.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		100	V
$I_{F(RMS)}$	RMS forward current		10	A
$I_{F(AV)}$	Average forward current	$T_c = 165^\circ\text{C} \quad \delta = 0.5$	5	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ sinusoidal	75	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ square $F = 1 \text{ kHz}$	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	2	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s} \quad T_j = 25^\circ\text{C}$	7200	W
T_{stg}	Storage temperature range		- 65 to + 175	°C
T_j	Maximum operating junction temperature *		175	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS5H100B

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	$^{\circ}\text{C}/\text{W}$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			3.5	μA
		$T_j = 125^{\circ}\text{C}$			1.3	4.5	mA
V_F^{**}	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 5\text{ A}$			0.73	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 5\text{ A}$		0.57	0.61	
		$T_j = 25^{\circ}\text{C}$	$I_F = 10\text{ A}$			0.85	
		$T_j = 125^{\circ}\text{C}$	$I_F = 10\text{ A}$		0.66	0.71	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$
 ** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.51 \times I_{F(AV)} + 0.02 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

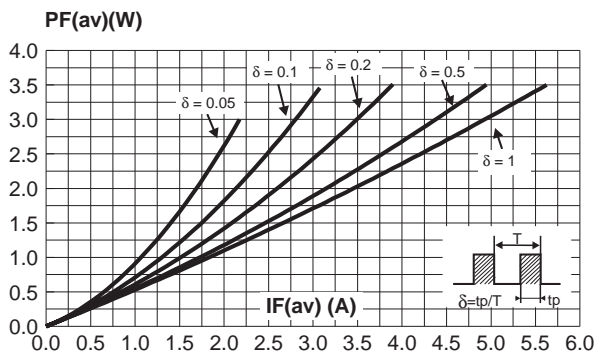


Fig. 3: Normalized avalanche power derating versus pulse duration.

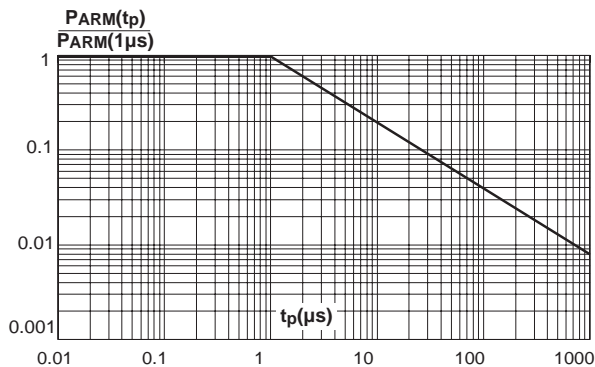


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

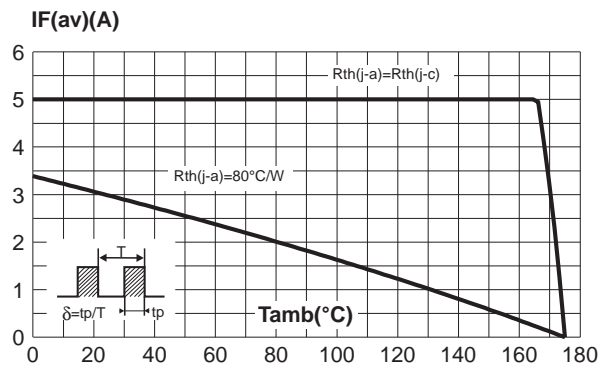


Fig. 4: Normalized avalanche power derating versus junction temperature.

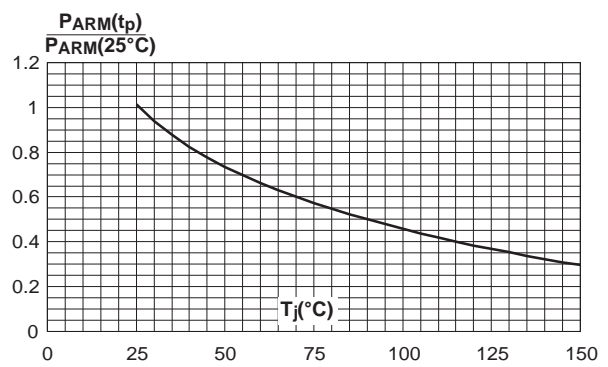


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

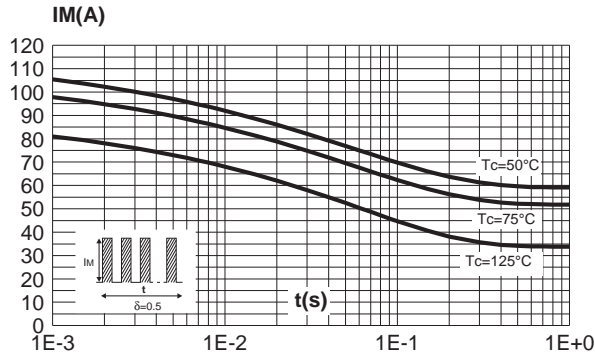


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

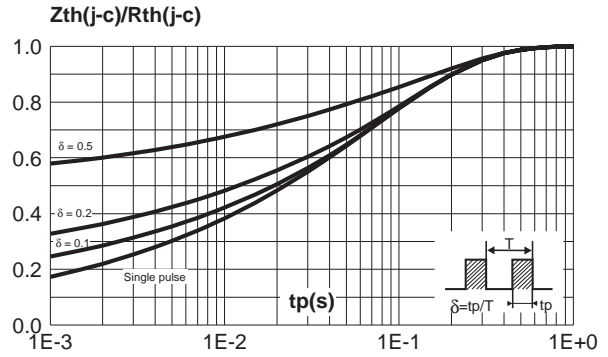


Fig. 7: Reverse leakage current versus reverse voltage applied.

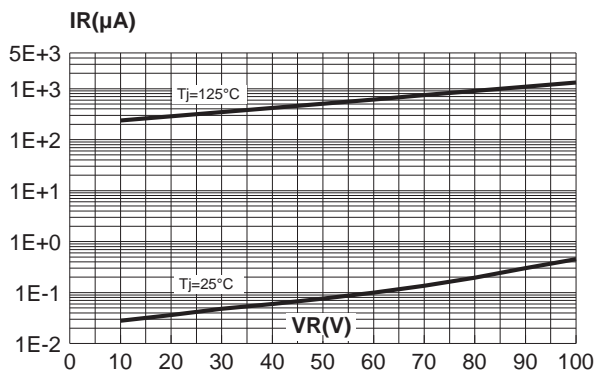


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

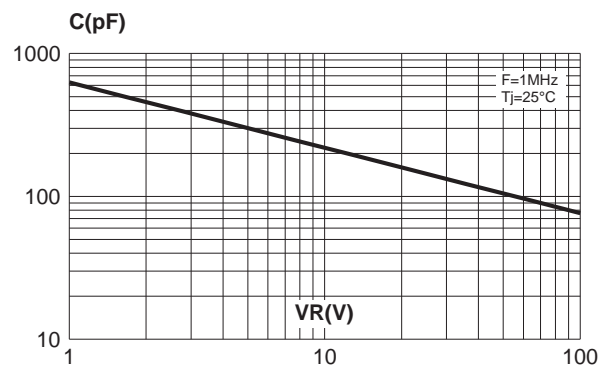


Fig. 9: Forward voltage drop versus forward current (maximum values).

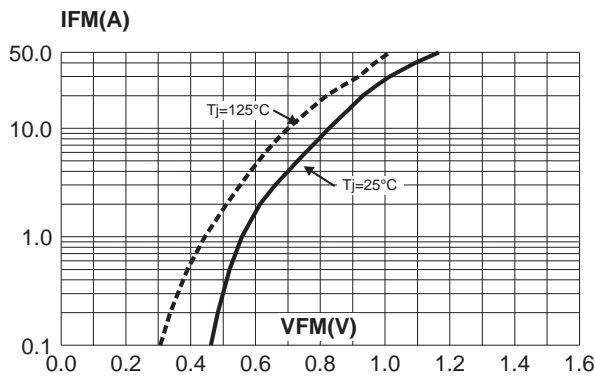
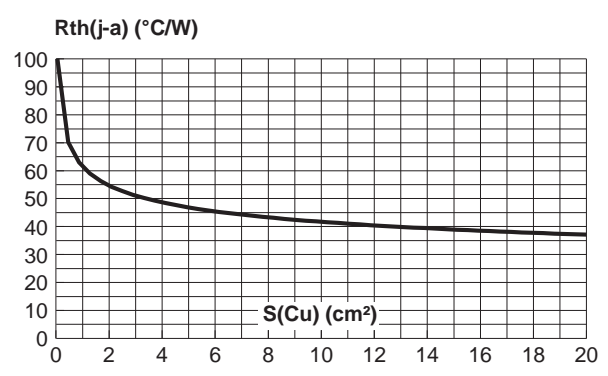
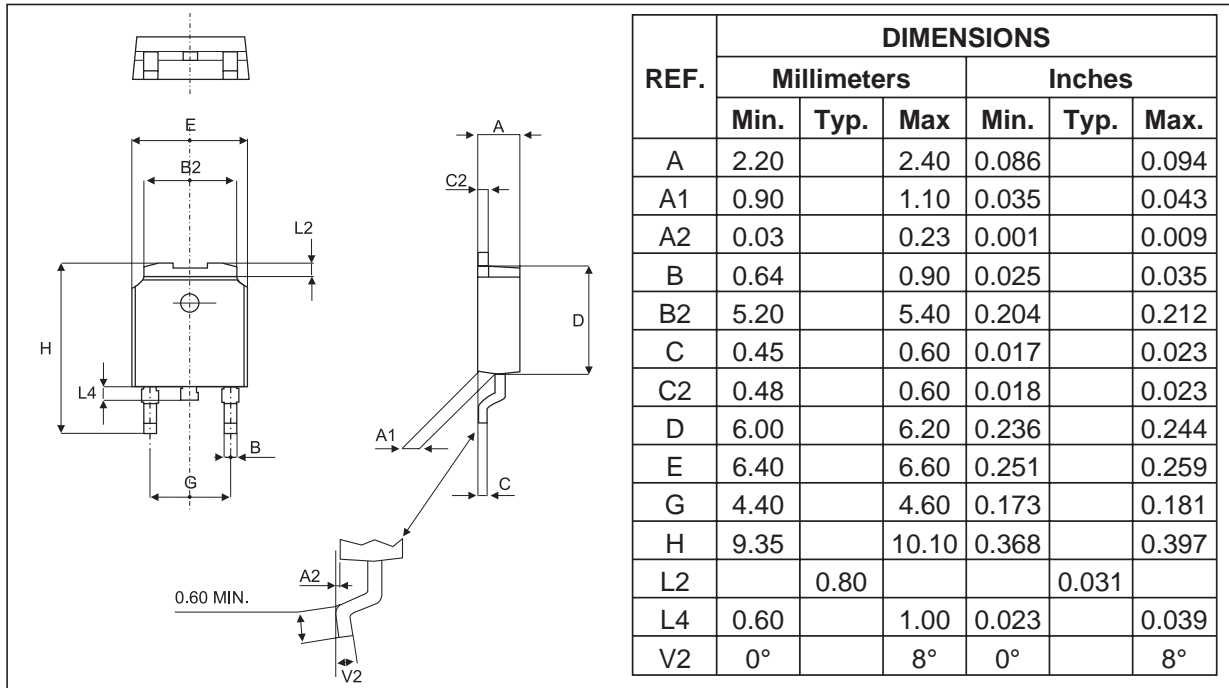


Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35μm).

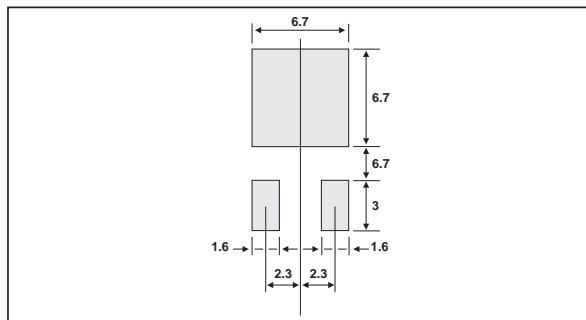


STPS5H100B

PACKAGE MECHANICAL DATA DPAK



FOOT PRINT (in millimeters)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS5H100B	S5H100	DPAK	0.30g	75	Tube
STPS5H100B-TR	S5H100	DPAK	0.30g	2500	Tape & reel

■ EPOXY MEETS UL94,V0

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